Silicon NPN High-Power Transistor

- . . . designed for general-purpose power amplifier and switching applications.
- Collector-Emitter Sustaining Voltage -

VCEO(sus) = 80 Vdc (Min)

DC Current Gain —

hFE = 20 (Min) @ IC = 6.0 Adc

 Low Collector — Emitter Saturation Voltage — VCE(sat) = 1.0 Vdc (Max) @ IC = 7.0 Adc

High Current — Gain–Bandwidth Product —
 fT = 4.0 MHz (Min) @ IC = 1.0 Adc

MAXIMUM RATINGS (1)

Rating	Symbol	Max	Unit
Collector–Emitter Voltage	VCEO	80	Vdc
Collector–Base Voltage	V _{CB}	80	Vdc
Emitter–Base Voltage	V _{EB}	5.0	Vdc
Collector Current — Continuous Peak	lC	15 30	Adc
Base Current	ΙΒ	5.0	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	160 0.915	Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θJC	1.1	°C/W

(1) Indicates JEDEC registered data. Units and conditions differ on some parameters and re-registration reflecting these changes has been requested. All above values meet or exceed present JEDEC registered data.

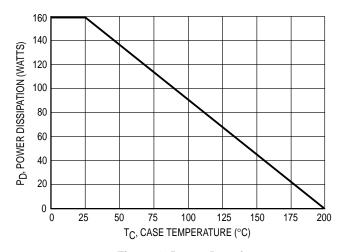


Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

2N5882

Motorola Preferred Device

15 AMPERE SILICON POWER TRANSISTOR 80 VOLTS 160 WATTS



CASE 1-07 TO-204AA (TO-3)

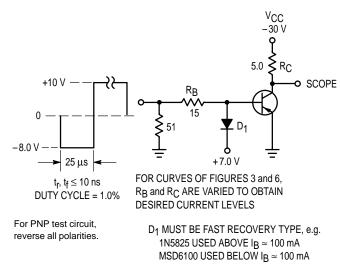


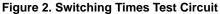
*ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS				•	
Collector–Emitter Sustaining Voltage (1) (IC = 200 mAdc, I _B = 0)		VCEO(sus)	80	_	Vdc
Collector Cutoff Current (VCE = 40 Vdc, IB = 0)		ICEO	_	1.0	mAdc
Collector Cutoff Current (VCE = 80 Vdc, VBE(off) = 1.5 (VCE = 80 Vdc, VBE(off) = 1.5	ICEX	_ _	0.5 5.0	mAdc	
Collector Cutoff Current (V _{CB} = 80 Vdc, I _E = 0)		ICBO	_	0.5	mAdc
Emitter Cutoff Current (V _{EB} = 5.	$0 \text{ Vdc, I}_{\mathbf{C}} = 0)$	I _{EBO}	_	1.0	mAdc
ON CHARACTERISTICS					
DC Current Gain (1) (IC = 2.0 Adc, V _{CE} = 4.0 Vdc) (IC = 6.0 Adc, V _{CE} = 4.0 Vdc) (IC = 15 Adc, V _{CE} = 4.0 Vdc)		hFE	35 20 4.0	_ 100 _	_
Collector–Emitter Saturation Voltage (1) (I _C = 7.0 Adc, I _B = 0.7 Adc) (I _C = 15 Adc, I _B = 3.75 Adc)		VCE(sat)		1.0 4.0	Vdc
Base–Emitter Saturation Voltage (1) (I _C = 15 Adc, I _B = 3.75 Adc)		V _{BE(sat)}	_	2.5	Vdc
Base–Emitter On Voltage (1) (I	V _{BE(on)}		1.5	Vdc	
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (2) (I _C = 1.0 Adc, V _{CE} = 10 Vdc, f _{test} = 1.0 MHz)		fΤ	4.0	_	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 100 \text{ kHz}$)		C _{ob}	_	400	pF
Small–Signal Current Gain (I _C = 2.0 Adc, V _{CE} = 4.0 Vdc, f = 1.0 kHz)		h _{fe}	20	_	_
SWITCHING CHARACTERISTICS	s				
Rise Time		t _r	_	0.7	μs
Storage Time	$(V_{CC} = 30 \text{ Vdc}, I_{C} = 6.0 \text{ Adc}, I_{B1} = I_{B2} = 0.6 \text{ Adc See Figure 2})$	t _S	_	1.0	μs
Fall Time	B1 - 1B2 - 0.0 / 100 000 / 19010 2)	t _f	1	0.8	μs

^{*} Indicates JEDEC Registered Data.

⁽²⁾ $f_T = |h_{fe}| \cdot f_{test}$.





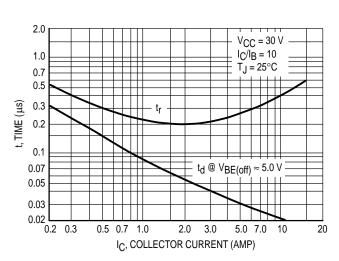


Figure 3. Turn-On Time

⁽¹⁾ Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

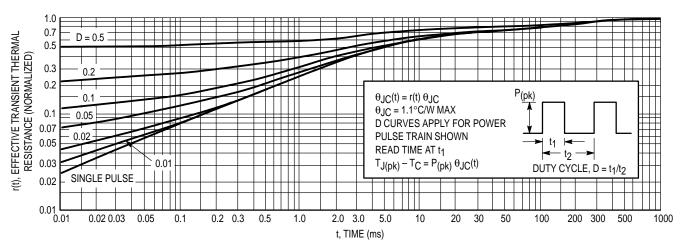


Figure 4. Thermal Response

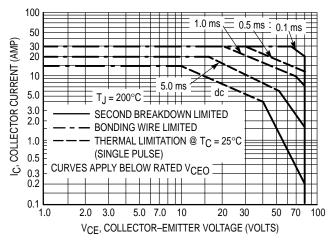


Figure 5. Active-Region Safe Operating Area

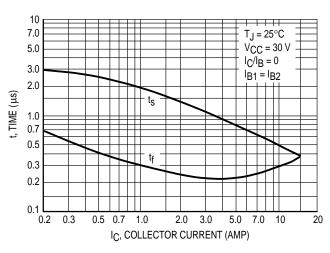


Figure 6. Turn-Off Time

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 200^{\circ}C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 200^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

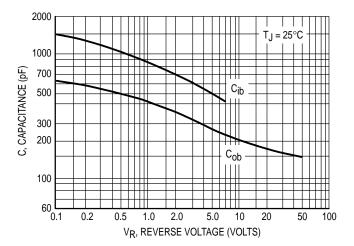
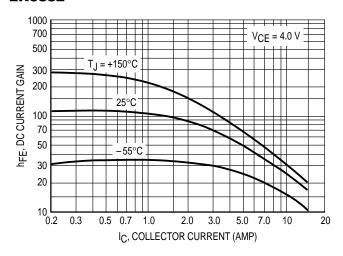


Figure 7. Capacitance

2N5882



2.0 1.6 1.2 0.8 0.03 0.05 0.07 0.1 0.2 0.3 0.5 0.7 1.0 2.0 3.0 I_B, BASE CURRENT (mAdc)

Figure 8. DC Current Gain

Figure 9. Collector Saturation Region

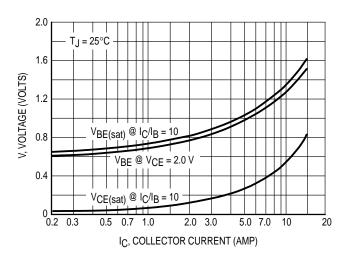
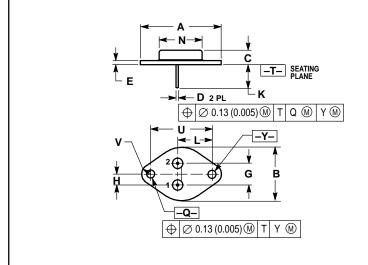


Figure 10. "On" Voltage

PACKAGE DIMENSIONS



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37 REF		
В	-	1.050		26.67	
С	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
E	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215 BSC		5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665 BSC		16.89 BSC		
N	_	0.830		21.08	
Q	0.151	0.165	3.84	4.19	
U	1.187 BSC		30.15 BSC		
٧	0.131	0.188	3.33	4.77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

CASE 1-07 TO-204AA (TO-3) ISSUE Z

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters which may be provided in Motorola data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and manufacture of the application

Mfax is a trademark of Motorola, Inc.

How to reach us:

USA/EUROPE/Locations Not Listed: Motorola Literature Distribution; JAPAN: Nippon Motorola Ltd.; SPD, Strategic Planning Office, 141, P.O. Box 5405, Denver, Colorado 80217. 1–303–675–2140 or 1–800–441–2447 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan. 81–3–5487–8488

Customer Focus Center: 1-800-521-6274

Mfax™: RMFAX0@email.sps.mot.com - TOUCHTONE 1-602-244-6609
Motorola Fax Back System - US & Canada ONLY 1-800-774-1848 - http://sps.motorola.com/mfax/

ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

HOME PAGE: http://motorola.com/sps/



> 2N5882/D